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R. Dyer

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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
Shusuke KAYA ET AL. : EXAMINER: HARMON, C.
SERIAL NO: 09/662,704 :
FILED: SEPTEMBER 15, 2000 : GROUP ART UNIT: 2881
FOR: SEMICONDUCTOR LASER DEVICE

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated January 15, 2002, please amend the above-identified application as follows.

IN THE CLAIMS

Please amend Claims 2 and 17 as follows:

a1 2. (Amended) The semiconductor laser device according to claim 19, wherein said low reflection film is formed from a single layer.

a2 17. (Amended) The semiconductor laser device according to any one of claims 1 to 16, wherein said Al_2O_3 film is deposited by an electron cyclotron resonance plasma sputtering process.

Please add new Claims 18 and 19 as follows:

a3 18. (New) A semiconductor laser device comprising:
a semiconductor multi-layer film comprising at least one confinement layer and at least one active layer;

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